



GP1M009A090H Information



For Reference Only

Part Number GP1M009A090H

Manufacturer Global Power Technologies Group

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 900V 9A TO220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









GP1M009A090H Specifications

Manufacturer Part Number	GP1M009A090H
Manufacturer	Global Power Technologies Group
Category	Discrete Semiconductor Products
	Transistors - FETs, MOSFETs - Single
Package	TO-220-3
Series	-
FET Type	N-Channel
Technology	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss)	900V
Current - Continuous Drain (Id) @ 25°C	9A (Tc)
Drive Voltage (Max Rds On, Min Rds On)	10V
Vgs(th) (Max) @ Id	4V @ 250μA
Gate Charge (Qg) (Max) @ Vgs	65nC @ 10V
Input Capacitance (Ciss) (Max) @ Vds	2324pF @ 25V
Vgs (Max)	±30V
FET Feature	-
Power Dissipation (Max)	290W (Tc)
Rds On (Max) @ Id, Vgs	1.4 Ohm @ 4.5A, 10V
Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type	Through Hole
Supplier Device Package	TO-220
Package / Case	TO-220-3
	Report errors?

GP1M009A090H Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

GP1M009A090H Payment Methods





















GP1M009A090H Shipping Methods













If you have any question about GP1M009A090H, please do not hesitate to contact us!

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